

IN THE TITLE:

Please amend the title in "clean" format, as follows:

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ELECTROLUMINESCENCE DISPLAY DEVICE WITH A DOUBLE GATE TYPE THIN FILM TRANSISTOR HAVING A LIGHTLY DOPED DRAIN STRUCTURE

IN THE CLAIMS:

Please amend claims 1, 9, 10, and 11 in "clean" format, as follows:

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1. (Twice Amended) An electroluminescence device, comprising:
an electroluminescence element having a light emissive layer provided between first and second electrodes;
a first thin film transistor receiving a selection signal at its gate to acquire a data signal; and
a second thin film transistor provided between a driving power supply and said electroluminescence element, and controlling power supplied from said driving power supply to said electroluminescence element in accordance with the data signal supplied from said first thin film transistor; wherein
said first thin film transistor is a double gate type having a lightly doped drain structure, said first thin film transistor has at least one of an n-channel, an offset structure, and a multigate structure; and
said second thin film transistor has a p-channel.

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9. (Twice Amended) An electroluminescence display device, comprising:
an electroluminescence element having a light emissive layer provided between an anode and a cathode;
a first thin film transistor having an active layer which is formed of a non-single crystalline semiconductor film and which includes a source connected to a storage capacitor, a drain connected to a drain signal line, and a gate electrode provided over a channel of said active layer and connected to a gate signal line; and
a second thin film transistor having an active layer which is formed of a non-single crystalline semiconductor film and which includes a drain connected to a driving power supply of said electroluminescence element, and a gate electrode connected to the source of said first thin film transistor; wherein
said first thin film transistor is a double gate type having a lightly doped drain structure, said first thin film transistor has at least one of an n-channel, an offset structure,

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Cont.

and a multigate structure; and

 said second thin film transistor has a p-channel.

10. (Twice Amended) An electroluminescence display device, comprising:
 an electroluminescence element having a light emissive layer provided between an
 anode and a cathode;

 a first thin film transistor having an active layer which is formed of a non-single
 crystalline semiconductor film and which includes a source connected to a storage capacitor,
 a drain connected to a drain signal line, and a gate electrode provided under a channel of said
 active layer and connected to a gate signal line; and

 a second thin film transistor having an active layer which is formed of a non-single
 crystalline semiconductor film and which includes a drain connected to a driving power
 supply of said electroluminescence element, and a gate electrode connected to the source of
 said first thin film transistor; wherein

 said first thin film transistor is a double gate type having a lightly doped drain
 structure, said first thin film transistor has at least one of an n-channel, an offset structure,
 and a multigate structure; and

 said second thin film transistor has a p-channel.

11. (Twice Amended) A light emissive device, comprising:
 a light emissive element having a light emissive layer provided between first and
 second electrodes;

 a first thin film transistor receiving a selection signal at its gate to acquire a data
 signal; and

 a second thin film transistor provided between a driving power supply and said
 element, and controlling power supplied from said driving power supply to said element in
 accordance with the data signal supplied from said first thin film transistor; wherein

 said first thin film transistor is a double gate type having a lightly doped drain
 structure, said first thin film transistor has at least one of an n-channel, an offset structure,
 and a multigate structure; and

 said second thin film transistor has a p-channel.